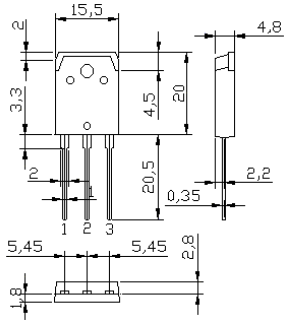
NPN SILICON TRIPLE DIFFUSED PLANAR TRANSISTOR

…designed for 140V/12A AF 60W output application.
…complementary to PMB817.

TO-3PI



1 : Base
2 : Collector (Heat Sink)
3 : Emitter

Weight: 4.5g Unit in mm

MAXIMUM RATINGS (T_a= 25 °C)

Characteristic	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	160	V
Collector Emitter Voltage	V_{CEO}	140	V
Emitter Base Voltage	V_{EBO}	6	V
Collector Current	I_C	12	A
Collector Current (Pulse)	I_{CP}	15	A
Collector Power Dissipation T_C= 25 °C	P_C	100	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-40 ~ 150	°C

ELECTRICAL CHARACTERISTICS (T_a= 25 °C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector Cutoff Current	I_{CBO}	V_{CB} = 80V, I_E = 0	-	-	0.1	mA
Emitter Cutoff Current	I_{EBO}	V_{EB} = 4V, I_C = 0	-	-	0.1	mA
DC Current Gain	$h_{FE(1)}$	V_{CE} = 5V, I_C = 1A	60	-	200	-
	$h_{FE(2)}$	V_{CE} = 5V, I_C = 6A	20	-	-	-
Transition Frequency	f_T	V_{CE} = 5V, I_C = 1A	-	15	-	MHz
Output Capacitance	C_{ob}	V_{CB} = 10V, f =1MHz	-	210	-	pF

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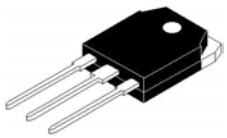
CLASSIFICATIONS OF $h_{FE(1)}$

Rank	D	E
Range	60 to 120	100 to 200



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